

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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HiPerFRED

 V_{RRM} 300 V

30 A

30 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Parallel legs

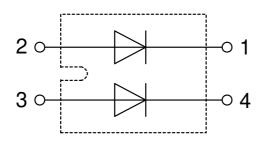
Part number

DSEP2x31-03A



Backside: isolated

F1 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~ • Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

20160920b

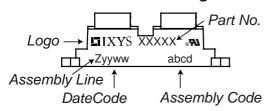


Fast Diode					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			300	V
V _{RRM}	max. repetitive reverse blocking ve	oltage	$T_{VJ} = 25^{\circ}C$			300	V
I _R	reverse current, drain current	$V_R = 300 \text{ V}$	$T_{VJ} = 25^{\circ}C$			10	μΑ
		$V_R = 300 \text{ V}$	$T_{VJ} = 150$ °C			1	mΑ
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			1.23	V
		$I_F = 60 \text{ A}$				1.40	٧
		$I_F = 30 \text{ A}$	T _{VJ} = 150°C			0.90	٧
		$I_F = 60 \text{ A}$				1.10	V
I _{FAV}	average forward current	T _C = 105°C	T _{VJ} = 150°C			30	Α
		rectangular $d = 0.5$					
V _{F0}	threshold voltage	and a decide Common by	T _{VJ} = 150°C			0.71	٧
\mathbf{r}_{F}	slope resistance	oss calculation only				6.2	mΩ
R _{thJC}	thermal resistance junction to case	е				1.15	K/W
R _{thCH}	thermal resistance case to heatsin	nk			0.10		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			100	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			300	Α
C	junction capacitance	$V_R = 150 \text{V} f = 1 \text{MHz}$	$T_{VJ} = 25^{\circ}C$		66		pF
I _{RM}	max. reverse recovery current	\	$T_{VJ} = 25 ^{\circ}\text{C}$		10		Α
		$I_F = 30 \text{ A}; V_R = 150 \text{ V}$	$T_{VJ} = 100^{\circ}C$		12.5		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 30 \text{ A; } V_R = 150 \text{ V} \\ -di_F /dt = 400 \text{ A/} \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		30		ns
	,	,	$T_{VJ} = 100^{\circ}C$		55		ns



Package SOT-227B (minibloc)			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					100	Α
T _{VJ}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T_{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{_{T}}$	terminal torque				1.1		1.5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air		3.2			mm		
d _{Spb/Apb}	creepage distance on suna	ce striking distance through an	terminal to backside 8.6		6.8			mm
V _{ISOL}	isolation voltage	t = 1 second			3000			٧
.002	t = 1 minute		50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		2500			٧

Product Marking

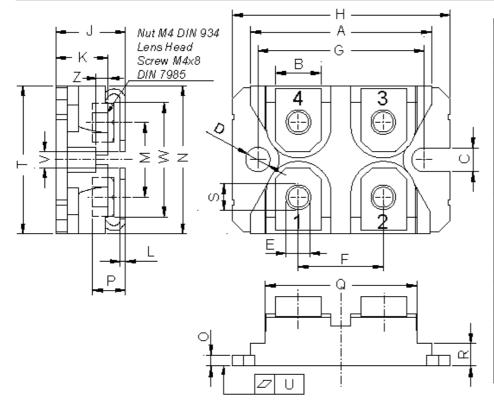


Ord	ering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Sta	ndard	DSEP2x31-03A	DSEP2x31-03A	Tube	10	473278

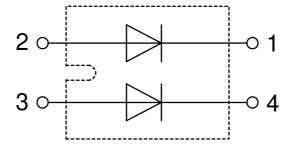
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	R_0	Fast Diode		
V _{0 max}	threshold voltage	0.71		V
$R_{0 \text{ max}}$	slope resistance *	4.3		$m\Omega$



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
Dim.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Z	2.50	2.70	0.098	0.106	





Fast Diode

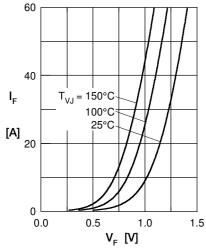


Fig. 1 Forward current I_F versus V_F

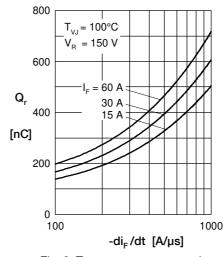


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

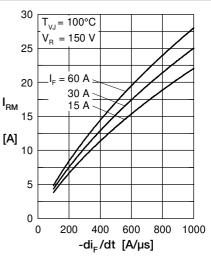


Fig. 3 Typ. peak reverse current I_{RM} versus -di_F/dt

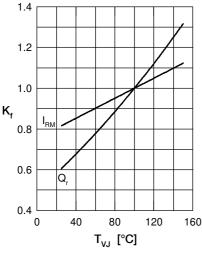


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

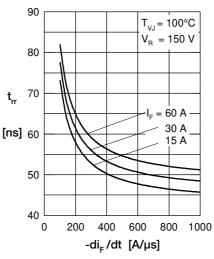


Fig. 5 Typ. recovery time t_{rr} versus $-di_{F}/dt$

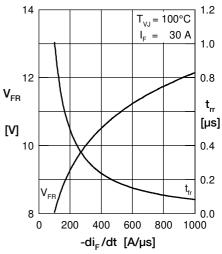


Fig. 6 Typ. peak forward voltage V_{FB} and tfr versus di_F/dt

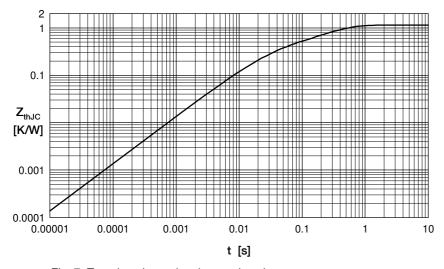


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{th,IC} calculation ...A:

i	$R_{thi} (K/W)$	t _i (s)
1	0.465	0.0052
2	0.179	0.0003
3	0.256	0.0397

Constants for Z_{th,IC} calculation ...AR:

İ	R_{thi} (K/W)	t _i (s)
1	0.368	0.0052
2	0.1417	0.0003
3	0.0295	0.0004
4	0.5604	0.0092